REFERENCES


55. St Onge, S., et al. *A 0.24 μm SiGe BiCMOS mixed-signal RF production technology featuring a 47 GHz f$_T$ HBT and 0.18 μm L$_{off}$ CMOS.* in *Proceedings of the 1999 Bipolar/BiCMOS Circuits and Technology Meeting.* 1999.


75. Ullán, M., et al., Radiation damage of SiGe HBT Technologies at different bias configurations, in Topical Workshop on Electronics for Particle Physics2008: Naxos, Greece.


117. Cressler, J.D (edt), *Fabrication of SiGe HBT BiCMOS technology* 2005: CRC Press INC, Boca Raton, USA.


